DATA SHEET

74LV4060

14-stage binary ripple counter with oscillator

Product specification

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Philips
Semiconductors

PHILIPS

14-stage binary ripple counter with oscillator 74LV4060

FEATURES

- Wide operating voltage: 1.0 to 5.5 V
- Optimized for Low Voltage applications: 1.0 to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical V_{OLP} (output ground bounce) < 0.8 V at V_{CC} = 3.3 V, T_{amb} = 25˚C.
- Typical V_{OHV} (output V_{OH} undershoot) > 2 V at V_{CC} = 3.3 V, T_{amb} = 25˚C.
- All active components on chip
- RC or crystal oscillator configuration
- Output capability: standard (except for R_{TC} and C_{TC})
- I_{CC} category: MSI

APPLICATIONS

- Control Counters
- Timers
- Frequency Dividers
- Time-delay circuits

DESCRIPTION

The 74LV4060 is a low-voltage Si-gate CMOS device and is pin and function compatible with the 74HC/HCT4060.

The 74LV4060 is a 14-stage ripple-carry counter/divider and oscillator with three oscillator terminals (RS, R_{TC} and C_{TC}), ten buffered outputs (Q_3 to Q_9 and Q_{11} to Q_{13}) and an overriding asynchronous master reset (MR). The oscillator configuration allows design of either RC or crystal oscillator circuits. The oscillator may be replaced by an external clock signal at input RS. In this case, keep the oscillator pins (R_{TC} and C_{TC}) floating.

The counter advances on the negative-going transition of RS. A HIGH level on MR resets the counter (Q_3 to Q_9 and Q_{11} to Q_{13} = LOW), independent of the other input conditions.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25˚C; $t_r = t_f \leq 2.5$ ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
	Propagation delay	C_L = 15 pF		
	RS to Q_3	V_{CC} = 3.3 V	29	
t_{PHL}/t_{PLH}	Q_n to Q_{n+1}		6	ns
t_{PHL}	MR to Q_n		16	
f_{max}	Maximum clock frequency		99	MHz
C_1	Input capacitance		3.5	pF
C_{PD}	Power dissipation capacitance per package	Notes 1, 2 and 3	40	pF

NOTES:

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW)
   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
   f_i = input frequency in MHz; C_L = output load capacity in pF;
   f_o = output frequency in MHz; V_{CC} = supply voltage in V;
   $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
2. The condition is V_1 = GND to V_{CC}
3. For formula on dynamic power dissipation, see the following pages.

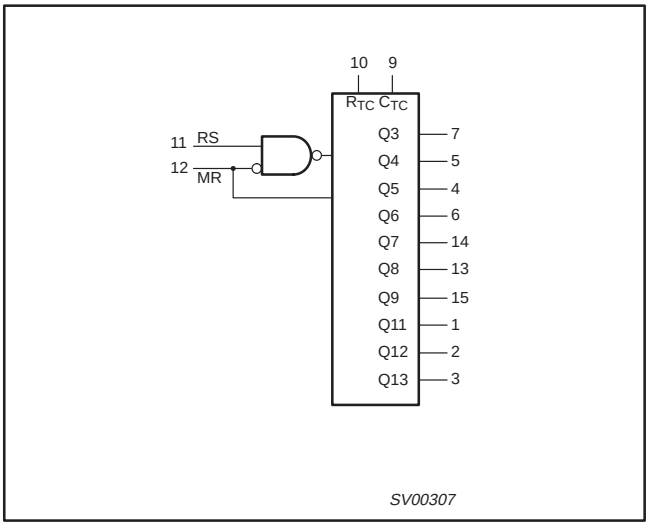
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
16-Pin Plastic DIL	–40°C to +125°C	74LV4060 N	74LV4060 N	SOT38-4
16-Pin Plastic SO	–40°C to +125°C	74LV4060 D	74LV4060 D	SOT109-1
16-Pin Plastic SSOP Type II	–40°C to +125°C	74LV4060 DB	74LV4060 DB	SOT338-1
16-Pin Plastic TSSOP Type I	–40°C to +125°C	74LV4060 PW	74LV4060PW DH	SOT403-1

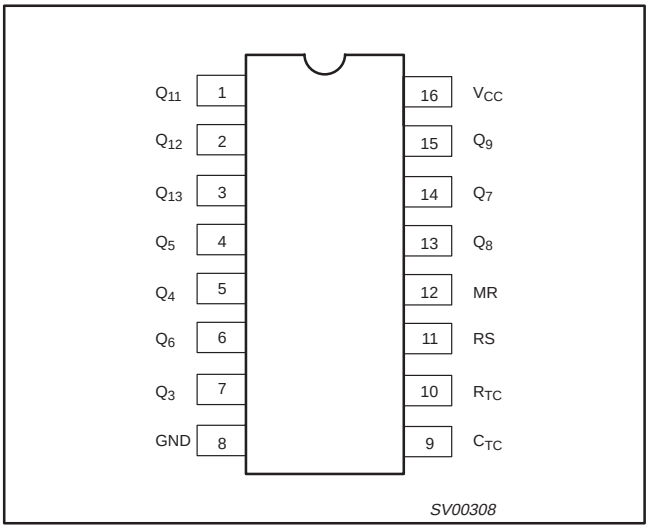
PIN DESCRIPTION

PIN NO.	SYMBOL	FUNCTION
1, 2, 3	Q_{11} to Q13	Counter outputs
7, 5, 4, 6, 15, 13, 15	Q_3 to Q_9	Counter outputs
8	GND	Ground (0 V)
9	C_{TC}	External capacitor connection
10	R_{TC}	External resistor connection
11	RS	Clock input/oscillator pin
12	MR	Master reset
16	V_{CC}	Positive supply voltage

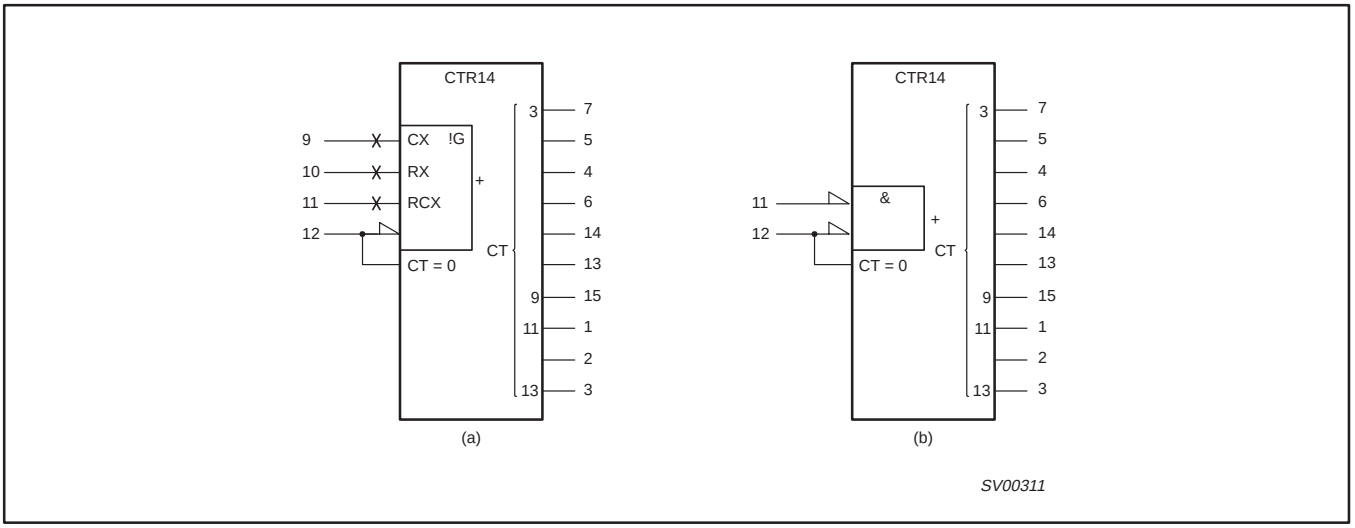
LOGIC SYMBOL



PIN CONFIGURATION



LOGIC SYMBOL (IEEE/IEC)



DYNAMIC POWER DISSIPATION

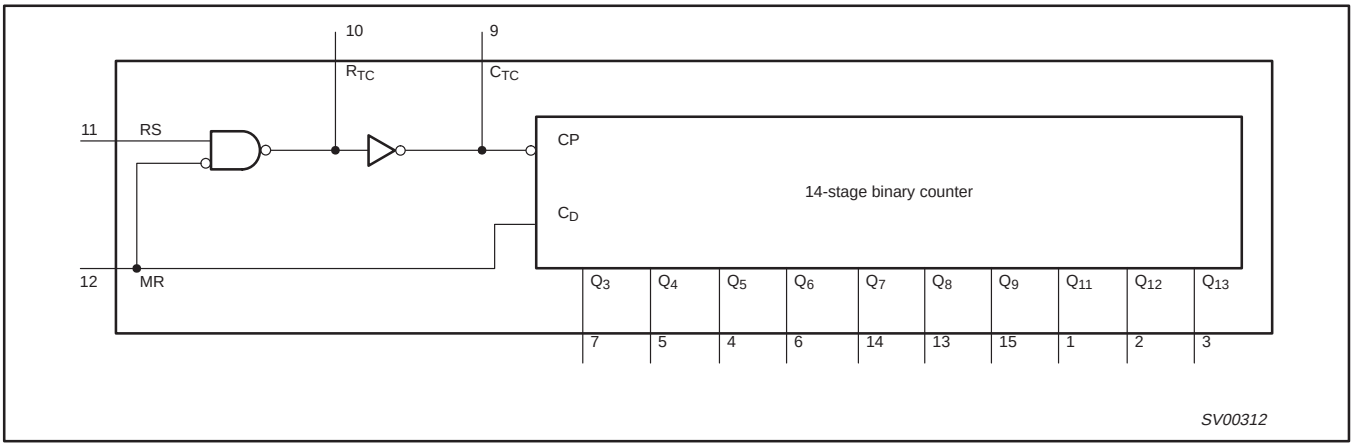
GND = 0 V; T_{amb} = 25 °C

PARAMETER	V_{CC} (V)	TYPICAL FORMULA FOR P_D (µW)[1]
Total dynamic power dissipation when using the on–chip oscillator (P_D)	1.2	$C_{PD} \times f_{osc} \times V_{CC}^2 + \Sigma (C_L \times V_{CC}^2 \times f_o) + 2C_t \times V_{CC}^2 \times f_{osc} + 16 \times V_{CC}$
	2.0	$C_{PD} \times f_{osc} \times V_{CC}^2 + \Sigma (C_L \times V_{CC}^2 \times f_o) + 2C_t \times V_{CC}^2 \times f_{osc} + 460 \times V_{CC}$
	3.0	$C_{PD} \times f_{osc} \times V_{CC}^2 + \Sigma (C_L \times V_{CC}^2 \times f_o) + 2C_t \times V_{CC}^2 \times f_{osc} + 1000 \times V_{CC}$

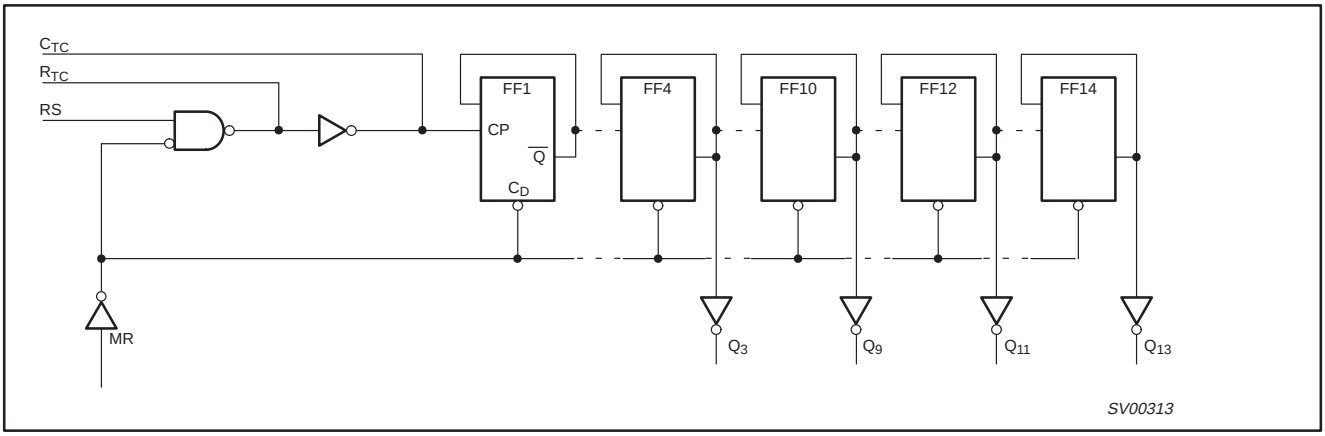
NOTE:

1. Where: f_o = output frequency in MHz; f_{osc} = oscillator frequency in MHz; $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs; C_L = output load capacitance in pF; C_t = timing capacitance in pF; V_{CC} = supply voltage in V.

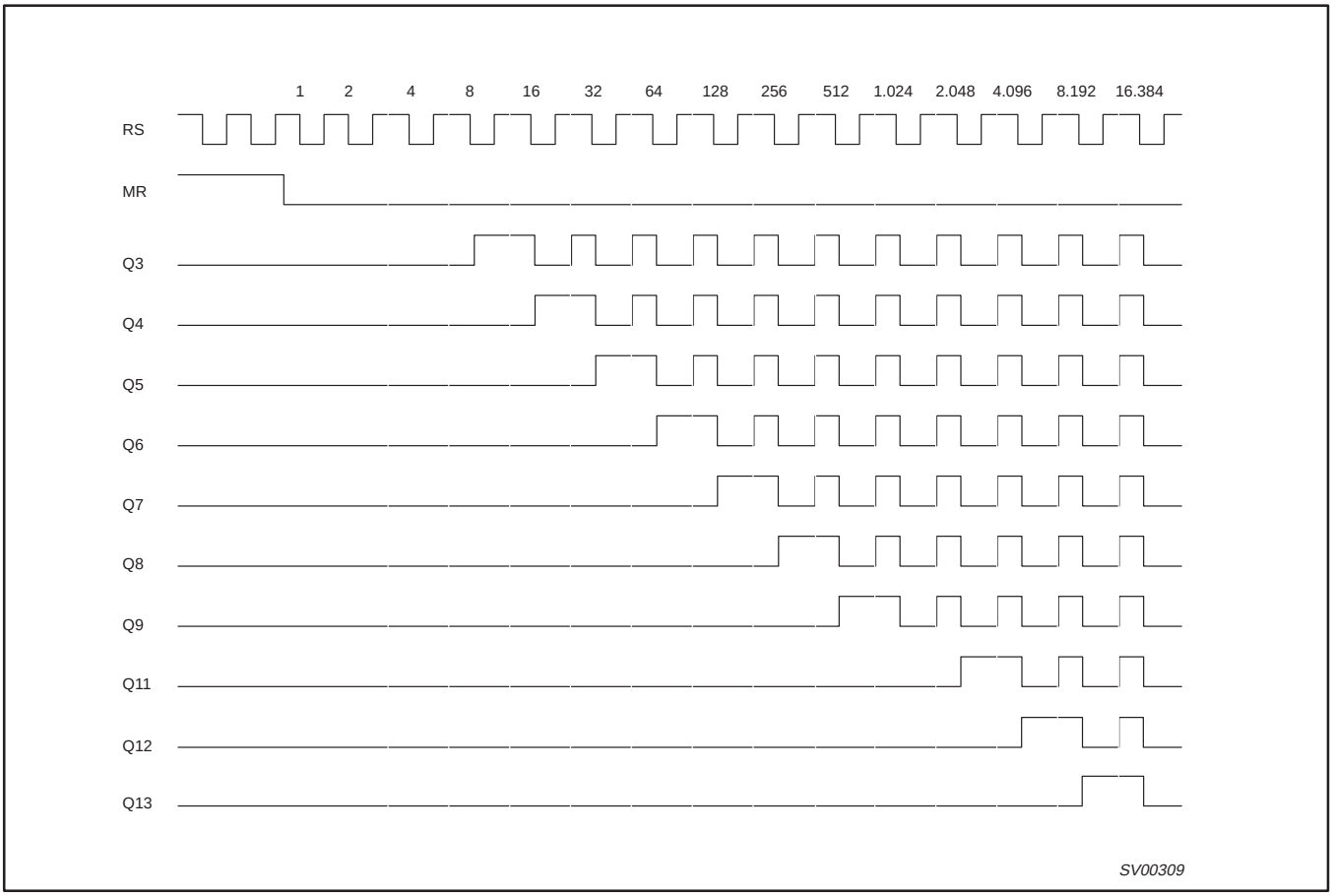
FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



TIMING DIAGRAM



ABSOLUTE MAXIMUM RATINGS[1, 2]

In accordance with the Absolute Maximum Rating System (IEC 134)
Voltages are referenced to GND (ground = 0V)

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		–0.5 to +7.0	V
$\pm I_{IK}$	DC input diode current	$V_I < –0.5$ or $V_I > V_{CC} + 0.5V$	20	mA
$\pm I_{OK}$	DC output diode current	$V_O < –0.5$ or $V_O > V_{CC} + 0.5V$	50	mA
$\pm I_O$	DC output source or sink current – standard outputs	$–0.5V < V_O < V_{CC} + 0.5V$	25	mA
$\pm I_{GND}$, $\pm I_{CC}$	DC V_{CC} or GND current for types with –standard outputs		50	mA
T_{stg}	Storage temperature range		–65 to +150	°C
P_{TOT}	Power dissipation per package –plastic DIL –plastic mini-pack (SO) –plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: –40 to +125°C above +70°C derate linearly with 12mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	 750 500 400	mW

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CC}	DC supply voltage	See Note[1]	1.0	3.3	5.5	V
V_I	Input voltage		0	–	V_{CC}	V
V_O	Output voltage		0	–	V_{CC}	V
T_{amb}	Operating ambient temperature range in free air	See DC and AC characteristics	–40 –40		+85 +125	°C
t_r, t_f	Input rise and fall times	V_{CC} = 1.0V to 2.0V V_{CC} = 2.0V to 2.7V V_{CC} = 2.7V to 3.6V V_{CC} = 3.6V to 5.5V	– – – –	– – – –	500 200 100 50	ns/V

NOTES:
1. The LV is guaranteed to function down to V_{CC} = 1.0V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2V to V_{CC} = 5.5V.

DC CHARACTERISTICS

Over operating conditions, voltages are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			-40°C to +85°C			-40°C to +125°C		
			MIN	TYP[1]	MAX	MIN	MAX	
V_{IH}	HIGH level Input voltage MR input	V_{CC} = 1.2V	0.9	–	–	0.9	–	V
		V_{CC} = 2.0V	1.4	–	–	1.4	–	
		V_{CC} = 2.7 to 3.6V	2.0	–	–	2.0	–	
		V_{CC} = 4.5 to 5.5V	0.7 * V_{CC}	–	–	0.7 * V_{CC}	–	
V_{IL}	LOW level Input voltage MR input	V_{CC} = 1.2V	–	–	0.3	–	0.3	V
		V_{CC} = 2.0V	–	–	0.6	–	0.6	
		V_{CC} = 2.7 to 3.6V	–	–	0.8	–	0.8	
		V_{CC} = 4.5 to 5.5	–	–	0.3 * V_{CC}	–	0.3 * V_{CC}	
V_{IH}	HIGH level Input voltage RS input	V_{CC} = 1.2V	1.0	–	–	1.0	–	V
		V_{CC} = 2.0V	1.6	–	–	1.6	–	
		V_{CC} = 2.7 to 3.6V	2.4	–	–	2.4	–	
		V_{CC} = 4.5 to 5.5V	0.8 * V_{CC}	–	–	0.8 * V_{CC}	–	
V_{IL}	LOW level Input voltage RS input	V_{CC} = 1.2V	–	–	0.2	–	0.2	V
		V_{CC} = 2.0V	–	–	0.4	–	0.4	
		V_{CC} = 2.7 to 3.6V	–	–	0.5	–	0.5	
		V_{CC} = 4.5 to 5.5	–	–	0.2 * V_{CC}	–	0.2 * V_{CC}	
V_{OH}	HIGH level output voltage; R_{TC} output	V_{CC} = 1.2V; RS = GND and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	V
		V_{CC} = 2.0V; RS = GND and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	
		V_{CC} = 2.7V; RS = GND and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = GND and MR = GND; $-I_O$ = 3.4mA	2.40	2.82	–	2.20	–	
		V_{CC} = 4.5V; RS = GND and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			-40°C to +85°C			-40°C to +125°C		
V_{OH}	HIGH level output voltage; R_{TC} output	V_{CC} = 1.2V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 0.8mA	–	–	–	–	–	V
		V_{CC} = 2.0V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 0.8mA	–	–	–	–	–	
		V_{CC} = 2.7V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 0.8mA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 0.8mA	2.40	2.82	–	2.20	–	
		V_{CC} = 4.5V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 0.8mA	–	–	–	–	–	
V_{OH}	HIGH level output voltage; R_{TC} output	V_{CC} = 1.2V; RS = GND and MR = GND; $-I_O$ = 100µA	1.0	1.2	–	1.0	–	V
		V_{CC} = 2.0V; RS = GND and MR = GND; $-I_O$ = 100µA	1.8	2.0	–	1.8	–	
		V_{CC} = 2.7V; RS = GND and MR = GND; $-I_O$ = 100µA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = GND and MR = GND; $-I_O$ = 100µA	2.8	3.0	–	2.8	–	
		V_{CC} = 4.5V; RS = GND and MR = GND; $-I_O$ = 100µA	–	–	–	–	–	
V_{OH}	HIGH level output voltage; R_{TC} output	V_{CC} = 1.2V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 100µA	1.0	1.2	–	1.0	–	V
		V_{CC} = 2.0V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 100µA	1.8	2.0	–	1.8	–	
		V_{CC} = 2.7V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 100µA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 100µA	2.8	3.0	–	2.8	–	
		V_{CC} = 4.5V; RS = V_{CC} and MR = V_{CC}; $-I_O$ = 100µA	–	–	–	–	–	
V_{OH}	HIGH level output voltage; C_{TC} output	V_{CC} = 1.2V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA		1.2	–	–	–	V
		V_{CC} = 2.0V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	
		V_{CC} = 2.7V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	2.40	2.82	–	2.20	–	
		V_{CC} = 4.5V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	
V_{OH}	HIGH level output voltage; except R_{TC} output	V_{CC} = 1.2V; V_I = V_{IH} and V_I = V_{IL}; $-I_O$ = 100µA	1.0	1.2	–	1.0	–	V
		V_{CC} = 2.0V; V_I = V_{IH} and V_I = V_{IL}; $-I_O$ = 100µA	1.8	2.0	–	1.8	–	
		V_{CC} = 2.7V; V_I = V_{IH} and V_I = V_{IL}; $-I_O$ = 100µA	–	–	–	–	–	
		V_{CC} = 3.0V; V_I = V_{IH} and V_I = V_{IL}; $-I_O$ = 100µA	2.8	3.0	–	2.8	–	
		V_{CC} = 4.5V; V_I = V_{IH} and V_I = V_{IL}; $-I_O$ = 100µA	–	–	–	–	–	

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			-40°C to +85°C			-40°C to +125°C		
V_{OH}	HIGH level output voltage; except R_{TC} and C_{TC} outputs	V_{CC} = 1.2V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	V
		V_{CC} = 2.0V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	
		V_{CC} = 2.7V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	
		V_{CC} = 3.0V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	2.40	2.82	–	2.20	–	
		V_{CC} = 4.5V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	
V_{OL}	LOW level output voltage; R_{TC} output	V_{CC} = 1.2V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	V
		V_{CC} = 2.0V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	
		V_{CC} = 2.7V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	–	0.25	0.40	–	0.50	V
		V_{CC} = 4.5V; RS = V_{CC} and MR = GND; $-I_O$ = 3.4mA	–	–	–	–	–	V
V_{OL}	LOW level output voltage; R_{TC} output	V_{CC} = 1.2V; RS = V_{CC} and MR = GND; $-I_O$ = 100µA	–	0	0.2	–	0.2	V
		V_{CC} = 2.0V; RS = V_{CC} and MR = GND; $-I_O$ = 100µA	–	0	0.2	–	0.2	
		V_{CC} = 2.7V; RS = V_{CC} and MR = GND; $-I_O$ = 100µA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = V_{CC} and MR = GND; $-I_O$ = 100µA	–	0	0.2	–	0.2	
		V_{CC} = 4.5V; RS = V_{CC} and MR = GND; $-I_O$ = 100µA	–	–	–	–	–	
V_{OL}	LOW level output voltage; C_{TC} output	V_{CC} = 1.2V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	V
		V_{CC} = 2.0V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	
		V_{CC} = 2.7V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	
		V_{CC} = 3.0V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	0.25	0.40	–	0.50	
		V_{CC} = 4.5V; RS = V_{IH} and MR = V_{IL}; $-I_O$ = 3.8mA	–	–	–	–	–	
V_{OL}	LOW level output voltage; except R_{TC} output	V_{CC} = 1.2V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 100µA	–	0	0.2	–	0.2	V
		V_{CC} = 2.0V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 100µA	–	0	0.2	–	0.2	
		V_{CC} = 2.7V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 100µA	–	–	–	–	–	
		V_{CC} = 3.0V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 100µA	–	0	0.2	–	0.2	
		V_{CC} = 4.5V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 100µA	–	–	–	–	–	

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			-40°C to +85°C			-40°C to +125°C		
V_{OL}	HIGH level output voltage; except R_{TC} and C_{TC} outputs	V_{CC} = 1.2V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	V
		V_{CC} = 2.0V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	
		V_{CC} = 2.7V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	0.25	0.40	–	0.50	
		V_{CC} = 3.0V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	
		V_{CC} = 4.5V; $V_I = V_{IH}$ and $V_I = V_{IL}$; $-I_O$ = 6mA	–	–	–	–	–	
I_I	Input leakage current	V_{CC} = 5.5V; $V_I = V_{CC}$ or GND	–	–	1.0	–	1.0	µA
I_{CC}	Quiescent supply current	V_{CC} = 3.6V; $V_I = V_{CC}$ or GND; I_O = 0	–	–	20	–	160	µA
	Quiescent supply current	V_{CC} = 5.5V; $V_I = V_{CC}$ or GND; I_O = 0	–	–	–	–	80	
ΔI_{CC}	Additional quiescent supply current per input pin	V_{CC} = 2.7V to 3.6V; $V_I = V_{CC}$ –0.6V; I_O = 0	–	–	500	–	850	µA

NOTE:
1. All typical values are measured at T_{amb} = 25°C.

AC CHARACTERISTICS

GND = 0V; $t_r = t_f$ = 2.5ns; C_L = 50pF; R_L = 500Ω

SYMBOL	PARAMETER	WAVEFORM	CONDITION	LIMITS –40 to +85 °C			LIMITS –40 to +125 °C		UNIT
			V_{CC}(V)	MIN	TYP[1]	MAX	MIN	MAX	
t_{PHL}/t_{PLH}	Propagation delay RS to Q_3	Figures, 6, 8	1.2	–	180	–	–	–	ns
			2.0	–	52	84	–	105	
			2.7	–	42	66	–	83	
			3.0 to 3.6	–	33[2]	53	–	66	
			4.5 to 5.5	–	24	39	–	49	
t_{PHL}/t_{PLH}	Propagation delay Q_n to Q_{n+1}	Figures 7, 8	1.2	–	40	–	–	–	ns
			2.0	–	14	23	–	29	
			2.7	–	10	16	–	20	
			3.0 to 3.6	–	8[2]	13	–	16	
			4.5 to 5.5	–	6	9	–	11	
t_{PHL}	Propagation delay MR to Q_n	Figures 7, 8	1.2	–	100	–	–	–	ns
			2.0	–	29	46	–	58	
			2.7	–	24	39	–	49	
			3.0 to 3.6	–	19[2]	31	–	39	
			4.5 to 5.5	–	14	23	–	29	
t_W	Clock pulse width RS; HIGH or LOW	Figure 6	2.0	34	9	–	38	–	ns
			2.7	25	6	–	30	–	
			3.0 to 3.6	20	5	–	24	–	
			4.5 to 5.5	16	4	–	20	–	
t_W	Master reset pulse width MR; HIGH	Figure 7	2.0	34	10	–	38	–	ns
			2.7	25	8	–	30	–	
			3.0 to 3.6	20	6	–	24	–	
			4.5 to 5.5	16	4	–	20	–	

SYMBOL	PARAMETER	WAVEFORM	CONDITION	LIMITS –40 to +85 °C			LIMITS –40 to +125 °C		UNIT
			V_{CC}(V)	MIN	TYP[1]	MAX	MIN	MAX	
t_{rem}	Removal time MR to RS	Figure 7	2.0	29	18	–	37	–	ns
			2.7	26	16	–	32	–	
			3.0 to 3.6	18	11	–	23	–	
			4.5 to 5.5	12	7	–	15	–	
f_{max}	Maximum clock pulse frequency	Figure 6	2.0	14	40	–	9	–	MHz
			2.7	19	70	–	12	–	
			3.0 to 3.6	24	90	–	15	–	
			4.5 to 5.5	30	100	–	19	–	

NOTE:
Unless otherwise stated, all typical values are at T_{amb} = 25°C.
1. Typical value measured at V_{CC} = 3.3V.
2. Typical value measured at V_{CC} = 5.0V.

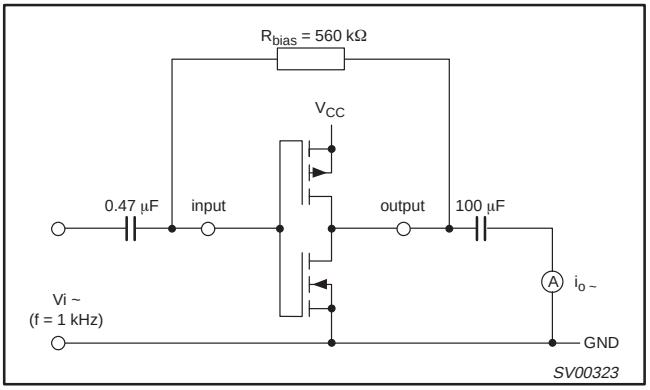


Figure 1.
Test set-up for measuring forward transconductance $g_{fs} = di_o/dv_i$ at v_o is constant (see also graph Figure 2); MR = LOW.

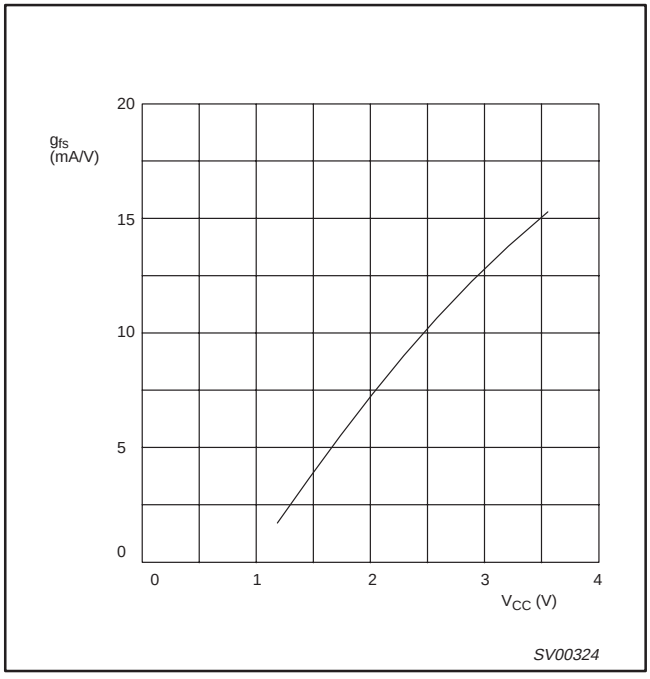


Figure 2.
Typical forward transconductance g_{fs} as a function of the supply voltage V_{CC} at T_{amb} = 25˚C.

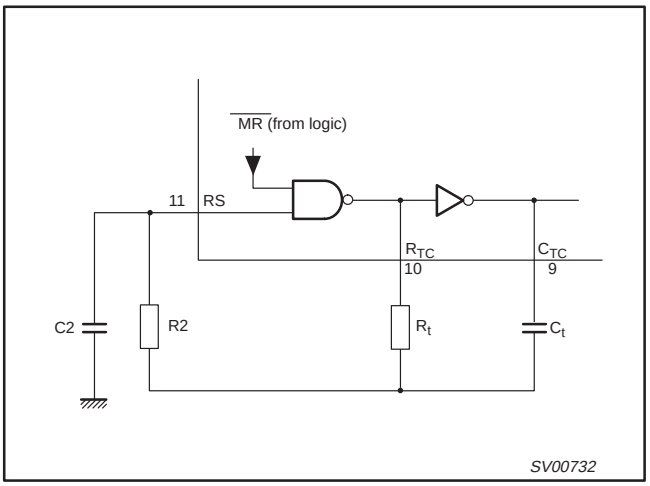


Figure 3.

Example of an RC oscillator. Typical formula for oscillator frequency:

$$f_{OSC} = \frac{1}{2.5 \times R_t \times C_t}$$

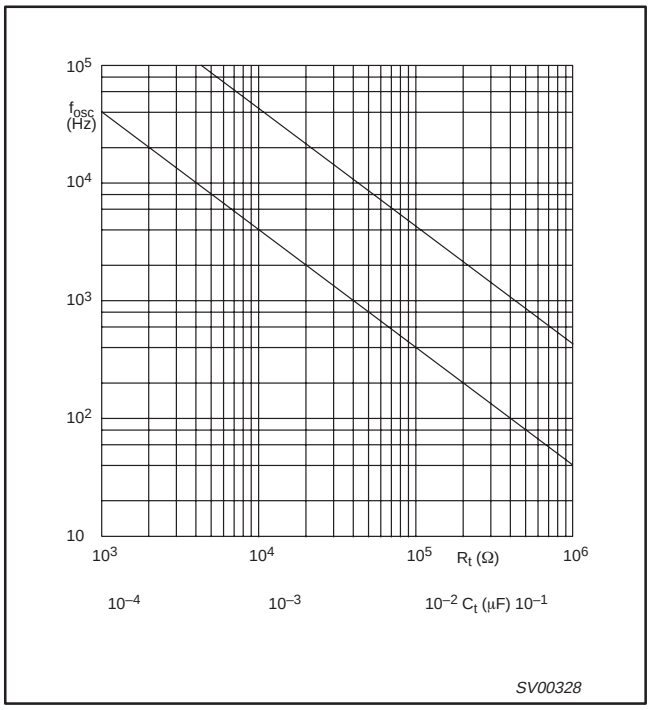


Figure 4.

RC oscillator frequency as a function of R_t and C_t at V_{CC} = 1.2 to 3.6 V; T_{amb} = 25˚C.
C_t curve at R_t = 100 kΩ; R2 = 200 kΩ.
R_t curve at C_t = 1 nF; R2 = 2 x R_t.

TIMING COMPONENTS LIMITATIONS

The oscillator frequency is mainly determined by $R_t \cdot C_t$, provided R2 ≈ 2R_t and R2 · C2 ≪ $R_t \cdot C_t$. The function of R2 is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C2 should be kept as small as possible. In consideration of accuracy, C_t must be larger than the inherent stray capacitance. R_t must be larger than the 'ON' resistance in series with it, which typically is 280 Ω at V_{CC} = 1.2 V, 130 Ω at V_{CC} = 2.0 V and 100 Ω at V_{CC} 3.0 V. The recommended values for these components to maintain agreement with the typical oscillation formula are: C_t > 50pF, up to any practical value, 10 kΩ < R_t < 1 MΩ. In order to avoid start-up problems, $R_t \geq$ 1 kΩ.

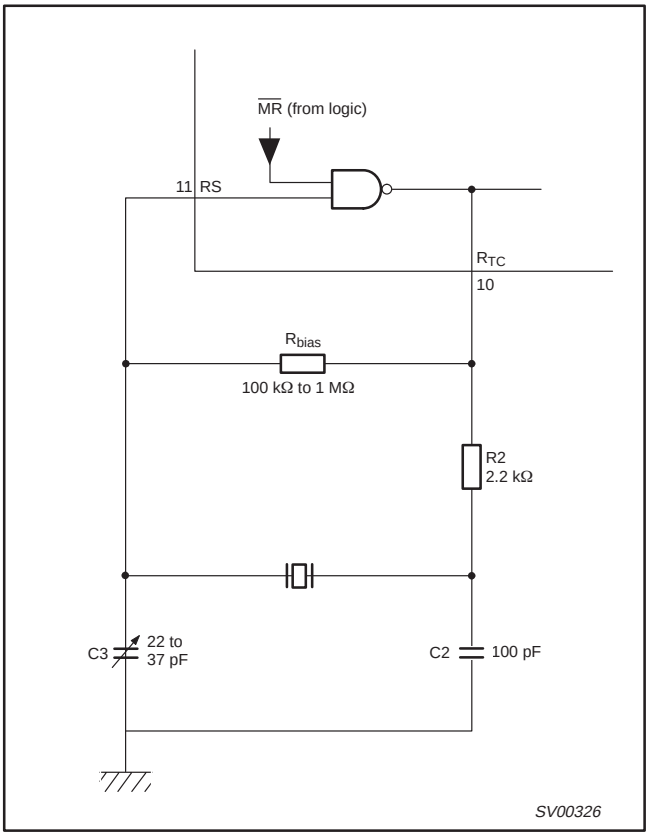


Figure 5. External components connection for a typical crystal oscillator

R2 is the power limiting resistor. For starting and maintaining oscillation, a minimum transconductance is necessary, so R2 should not be too large. A practical value for R2 is 2.2 kΩ.

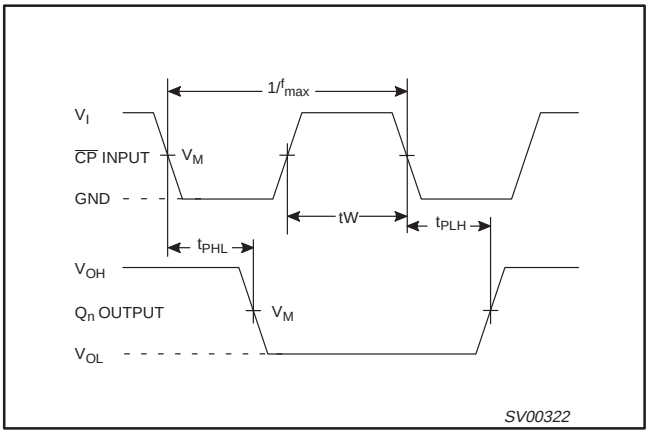


Figure 6.

Waveforms showing the clock (RS) to output (Q_3) propagation delays, the clock pulse width, the output transition times and the maximum clock frequency.

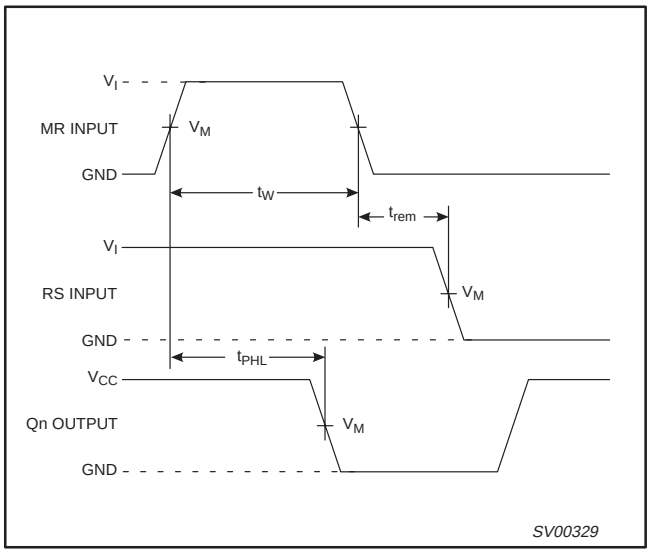


Figure 7.

Waveforms showing the master reset (MR) pulse width, the master reset to output (Q_n) propagation delays and the master reset to clock (RS) removal time.

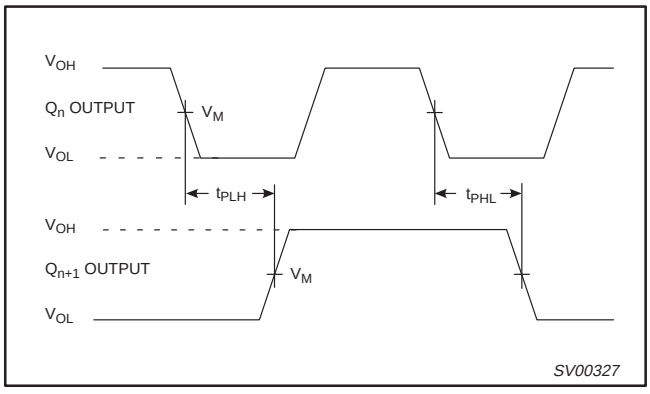


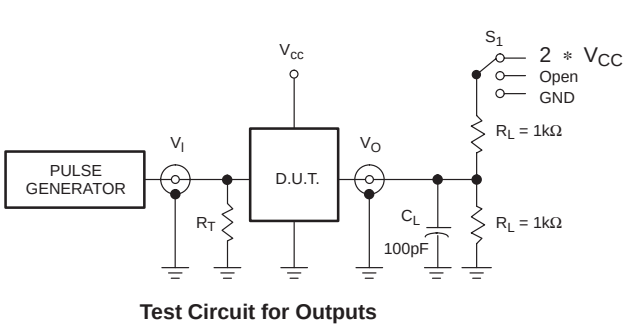
Figure 8.

Waveforms showing the output Q_n to output $_{n+1}$ propagation delays.

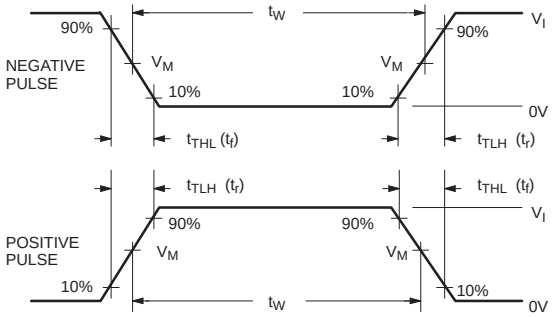
NOTES:

1. $V_M = 1.5$ V at $V_{CC} \geq 2.7$ V and ≤ 3.6 V
   $V_M = 0.5 \cdot V_{CC}$ at $V_{CC} < 2.7$ V and ≥ 4.5 V.
2. V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.

TEST CIRCUIT



Test Circuit for Outputs



V_M = 1.5V
Input Pulse Definition

SWITCH POSITION

TEST	S_1
t_{PLH}/t_{PHL}	Open

V_{CC}	V_I
< 2.7V	V_{CC}
2.7–3.6V	2.7V
≥ 4.5 V	V_{CC}

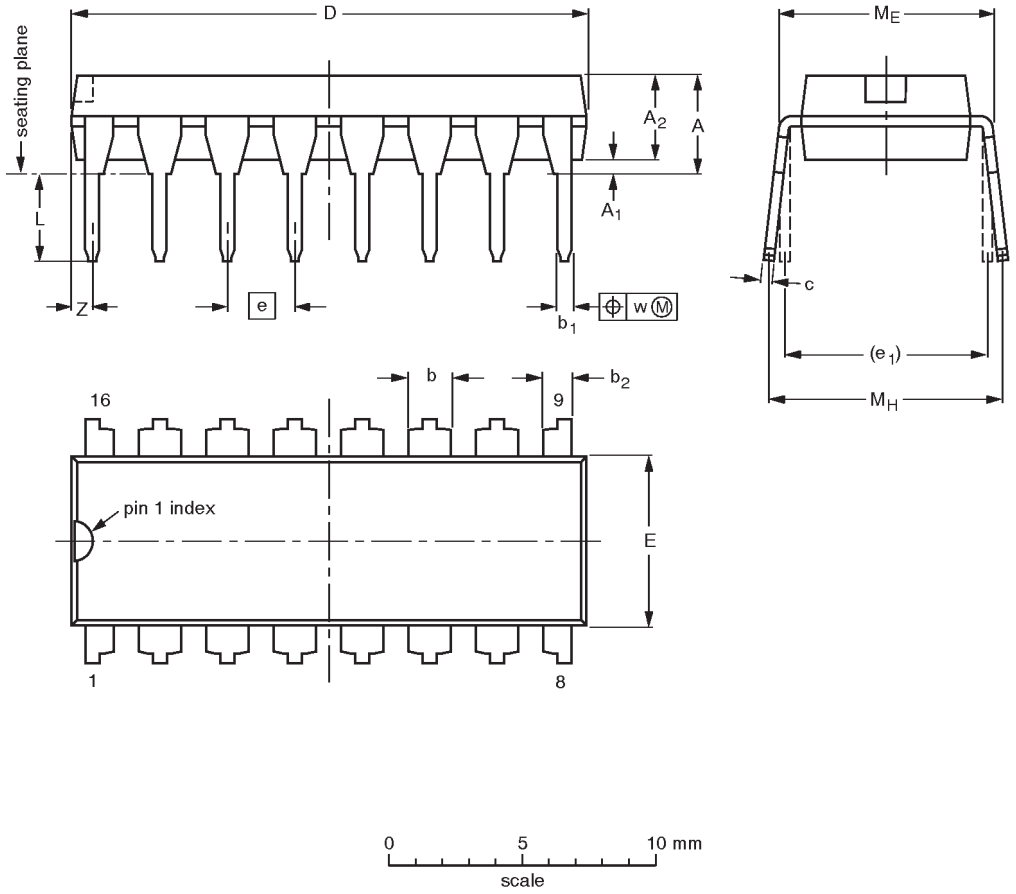
DEFINITIONS

R_L = Load resistor
C_L = Load capacitance includes jig and probe capacitance
R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

SV00910

Figure 9. Load circuitry for switching times.

DIP16: plastic dual in-line package; 16 leads (300 mil) **SOT38-4**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

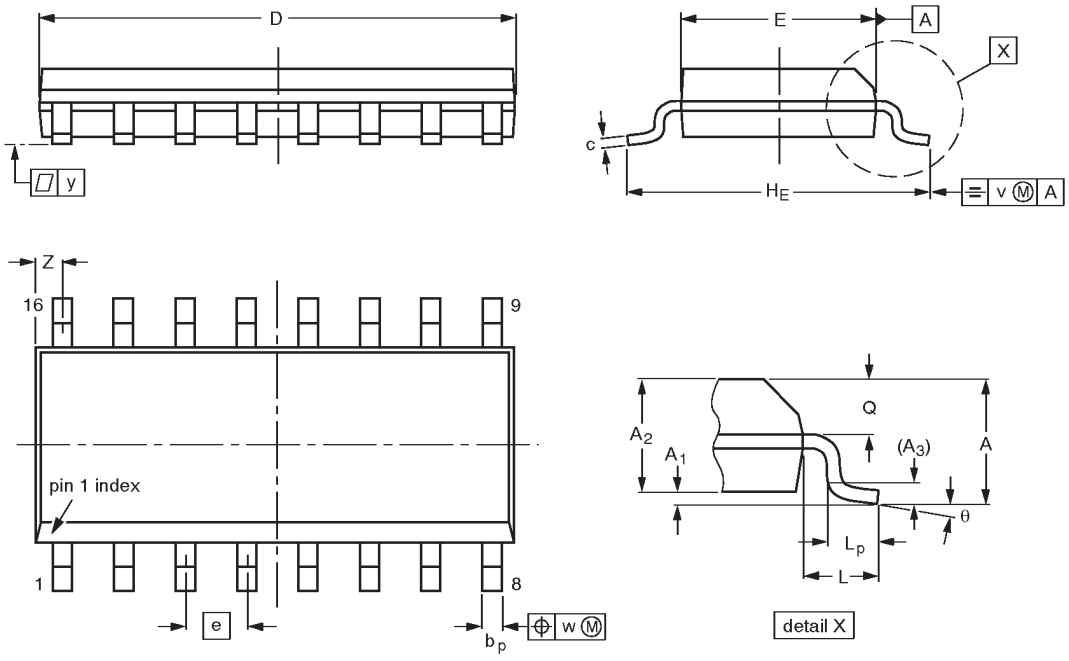
UNIT	A max.	A_1 min.	A_2 max.	b	b_1	b_2	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.030

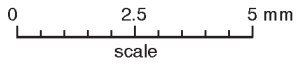
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT38-4						~~92-11-17~~ 95-01-14

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**





DIMENSIONS (inch dimensions are derived from the original mm dimensions)

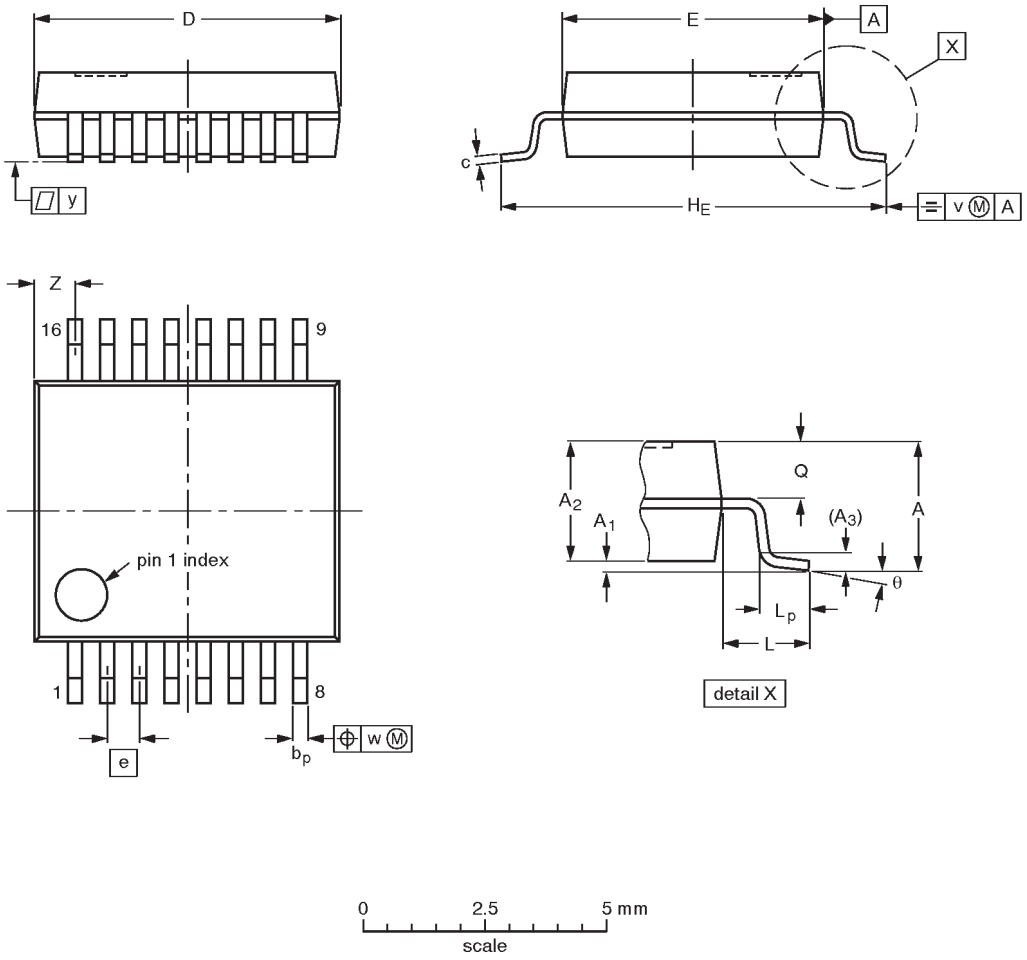
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.0098 0.0039	0.057 0.049	0.01	0.019 0.014	0.0098 0.0075	0.39 0.38	0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT109-1	076E07S	MS-012AC				~~91-08-13~~ 95-01-23

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

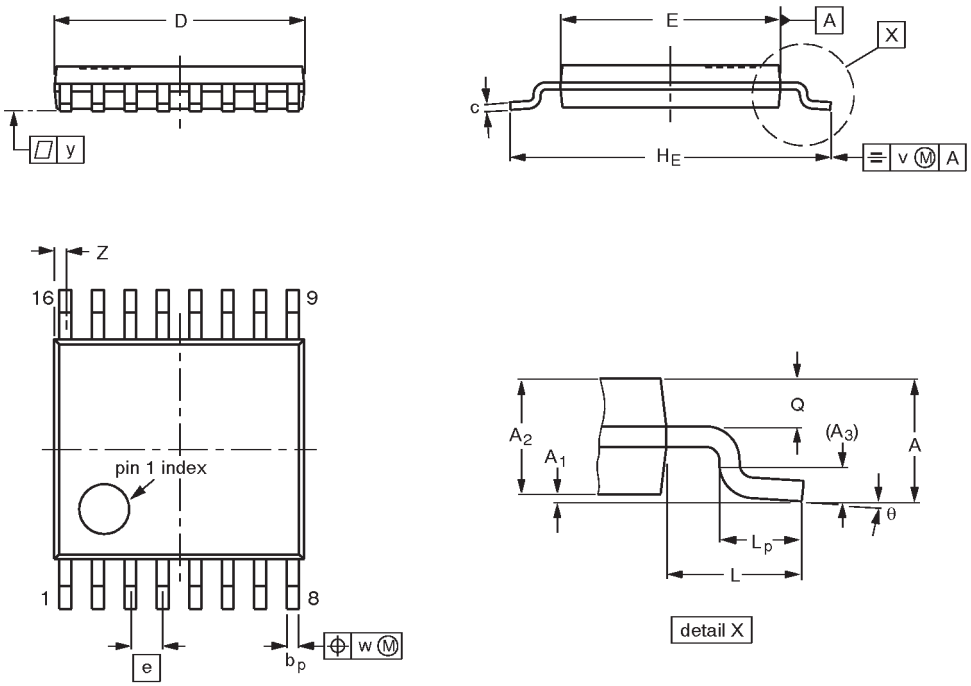
UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

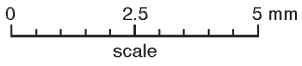
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT338-1		MO-150AC				~~94-01-14~~ 95-02-04

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**





DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT403-1		MO-153				~~94-07-12~~ 95-04-04

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